Title (en)

Method of polishing semiconductor wafer.

Title (de)

Verfahren zum Polieren von Halbleiterplättchen.

Title (fr)

Procédé de polissage de plaquettes semi-conductrices.

Publication

EP 0403287 A2 19901219 (EN)

Application

EP 90306519 A 19900614

Priority

JP 15374889 A 19890616

Abstract (en)

A semiconductor wafer (12) is ground or polished to a desired thickness by pressing the wafer against a rotating turntable (13), characterised in that the semiconductor wafer is bonded to a plate (11), and a thickness-regulating member (15) whose surface is more resistant to polishing/grinding than the semiconductor wafer is arranged on the plate. By way of example, the thickness-regulating member comprises a silicon matrix and has a silicon oxide film at the surface.

IPC 1-7

B24B 37/04; H01L 21/00

IPC 8 full level

B24B 37/07 (2012.01); **H01L 21/304** (2006.01)

CPC (source: EP)

B24B 37/013 (2013.01)

Cited by

CN105199610A; EP0561532A3; GB2275130A; GB2275130B; US5445996A; US5914275A; US5948205A

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DE FR GB

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